



**ZXTP03200BG** 

200V PNP MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223

### **Features**

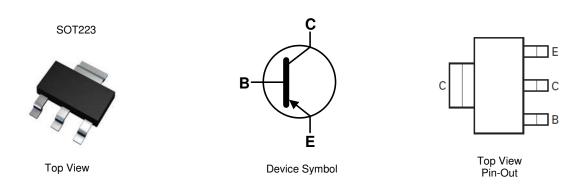
- $BV_{CEO} > -200V$
- I<sub>C</sub> = -2A High Continuous Collector Current
- I<sub>CM</sub> = -5A Peak Pulse Current
- Low Saturation Voltage  $V_{CE(sat)}$  < -160mV @ I<sub>C</sub> = -1A
- $R_{SAT} = 135m\Omega$  for a Low Equivalent On-Resistance
- Enhanced Switching Performance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

# Applications

DC-DC Conversion

## **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)



## Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP03200BGTA	ZXTP03200B	7	12	1,000
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.				

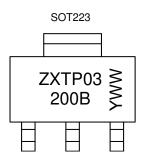
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied. 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



ZXTP03200B = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{WW}$  = Week Code (01~53)



## Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-220	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-200	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	Ic	-2	А
Peak Pulse Current	I <sub>CM</sub>	-5	А
Base Current	IB	-1	А

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		1.25		
Power Dissipation	(Note 6)	D D	1.65	w	
Power Dissipation	(Note 7)	PD	3.0	vv	
	(Note 8)		5.8		
	(Note 5)		100		
Thermal Resistance. Junction to Ambient	(Note 6)	D	76		
mermai nesistance, sunction to Amblent	(Note 7)	$R_{ ext{ heta}JA}$	41.6	°C/W	
	(Note 8)		21.5		
Thermal Resistance, Junction to Lead	(Note 9)	$R_{\theta JL}$	10.5		
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C		

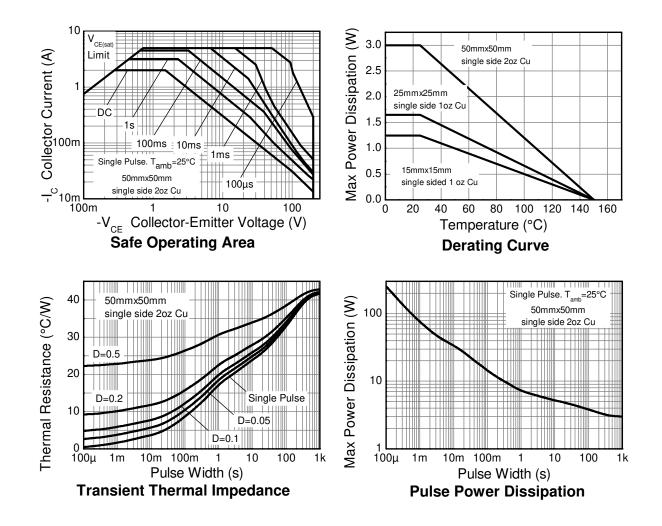
# ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

 For a device mounted with the collector lead on 15mm x 15mm 1oz. copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
Same as Note 5, except the device is mounted on 25mm x 25mm 1oz. copper.
Same as Note 5, except the device is mounted on 50mm x 50mm 2oz. copper.
Same as Note 7, except measured at t<5 seconds.</li>
Thermal resistance from junction to solder-point (at the end of the collector lead).
Refer to JEDEC specification JESD22-A114 and JESD22-A115. Notes:



# **Thermal Characteristics and Derating Information**





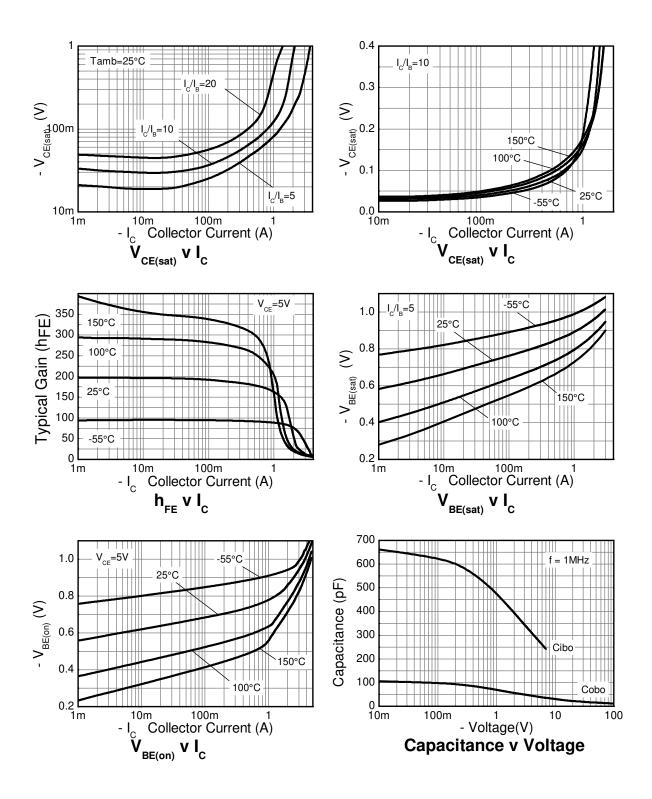
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-220	-245	-	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV <sub>CER</sub>	-220	-245	-	V	$I_{C} = -1\mu A, R_{B} \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 11)	BV <sub>CEO</sub>	-200	-225	-	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	-8.4	-	V	I <sub>E</sub> = -100μA
Collector Cut-Off Current		-	< -1	-50	nA	V <sub>CB</sub> = -200V
	ICBO	-	-	-0.5	μA	$V_{CB} = -200V, T_A = +100^{\circ}C$
Emitter Cut-Off Current	I <sub>EBO</sub>	-	< -1	-10	nA	$V_{EB} = -6V$
		100	195	-		$I_{C} = -10 \text{mA}, V_{CE} = -5 \text{V}$
DC Current Transfer Statia Datia (Nata 11)	h	100	170	300	-	$I_{C} = -1A, V_{CE} = -5V$
DC Current Transfer Static Ratio (Note 11)	h <sub>FE</sub>	20	50	-		$I_{C} = -2A, V_{CE} = -5V$
		-	5	-		$I_{C} = -5A, V_{CE} = -5V$
		-	-37	-50	mV	I <sub>C</sub> = -0.1A, I <sub>B</sub> = -10mA
Collector Emitter Coturation Makers (Nate 11)		-	-130	-155		$I_{\rm C} = -0.5 \text{A}, I_{\rm B} = -25 \text{mA}$
Collector-Emitter Saturation Voltage (Note 11)	V <sub>CE(sat)</sub>	-	-135	-160		I <sub>C</sub> = -1A, I <sub>B</sub> = -100mA
		-	-180	-275		$I_{C} = -2A, I_{B} = -400 \text{mA}$
Base-Emitter Saturation Voltage (Note 11)	V <sub>BE(sat)</sub>	-	-955	-1,100	mV	$I_{\rm C} = -2A, I_{\rm B} = -400 \text{mA}$
Base-Emitter Turn-On Voltage (Note 11)	V <sub>BE(on)</sub>	-	-860	-1,000	mV	$I_{C} = -2A, V_{CE} = -5V$
Transitional Frequency (Note 11)	f <sub>T</sub>	-	105	-	MHz	$I_{C} = -100 \text{mA}, V_{CE} = -10 \text{V}, f = 50 \text{MHz}$
Output Capacitance	Cobo	-	31	-	pF	V <sub>CB</sub> = -10V, f = 1MHz
Delay Time	t <sub>d</sub>		21	-		
Rise Time	tr		18	-	]	$V_{CC} = -50V, I_{C} = -1A,$
Storage Time	ts	-	680	-	ns	$I_{B1} = -I_{B2} = -100 \text{mA}$
Fall Time	t <sub>f</sub>	-	75	-		

Note: 11. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



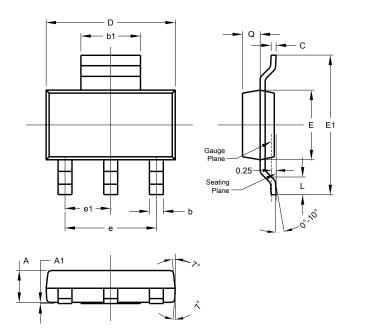
# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





## **Package Outline Dimensions**

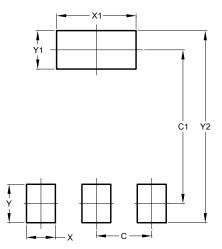
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
e	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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